

0039-7684-2SRD DIV



#12/Amend E
R. Ford
12/5/11

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

HISAKO AOYAMA ET AL. / :

EXAMINER: EATON, K.

SERIAL NO: 09/558,053 :

FILED: APRIL 26, 2000

GROUP ART UNIT: 2823

FOR: SEMICONDUCTOR DEVICE AND:
PROCESS OF FABRICATING THE
SAME

RECEIVED
EPO-3 2011
TECHNOLOGY CENTER 2011

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office dated August 29, 2001, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claim 29 as shown on the marked-up copy to read as follows:

Sub
29. (Amended) A process of fabricating a semiconductor device comprising:
forming a first insulating film on a semiconductor substrate;
forming a second insulating film on said first insulating film, said second insulating film being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;